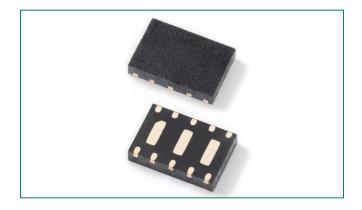
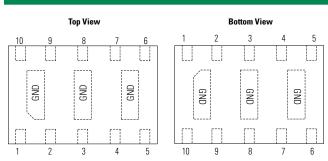


# SP2555NUTG 2.5V 45A Diode Array



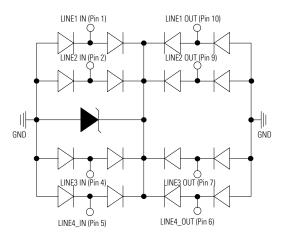


#### Pinout



NOTE: PIN3, PIN8 are same potential with GND

#### **Functional Block Diagram**



Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

#### Description

The SP2555NUTG is a low-capacitance, TVS Diode Array designed to provide protection against ESD (electrostatic discharge), CDE (cable discharge events), EFT (electrical fast transients), and lightning induced surges for highspeed, differential data lines. It's packaged in a µDFN package (3.0 x 2.0mm) and each component can protect up 4 channels or 2 differential pairs, up to 45A (IEC 61000-4-5 2<sup>nd</sup> edition,) and up to 30kV ESD (IEC 61000-4-2). The "flow-through" design minimizes signal distortion, reduces voltage overshoot, and provides a simplified PCB design.

The SP2555NUTG with its low capacitance and low clamping voltage makes it ideal for high-speed data interfaces such as 1GbE applications found in notebooks, switches, etc.

#### Features

- ESD, IEC 61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC 61000-4-4, 40A (5/50ns)
- Lightning, 45A (8/20µs as defined in IEC 61000-4-5 2nd Edition)
- Low capacitance of 2.5pF@0V (TYP) per I/O
- Low leakage current of 0.1µA (TYP) at 2.5V
- µDFN-10 package is optimized for high-speed data line routing
- · Provides protection for two differential data pairs (4 channels) up to 45A
- · Low operating and clamping voltage
- AEC-Q101 gualified
- Halogen free, Lead free and RoHS compliant

### Applications

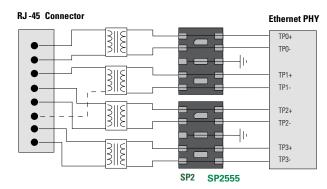
Notebooks

•10/100/1000 Ethernet

Desktops, Servers and

- LVDS Interfaces WAN/LAN Equipment
  - Integrated Magnetics
  - Smart TV

#### **Application Example**





#### **Absolute Maximum Ratings**

Symbol	Parameter	Value	Units
I <sub>PP</sub>	Peak Current (t <sub>e</sub> =8/20µs)	45	A
P <sub>Pk</sub>	Peak Pulse Power (t <sub>p</sub> =8/20µs)	1000	W
T <sub>OP</sub>	Operating Temperature	-40 to 125	°C
T <sub>STOR</sub>	Storage Temperature	-55 to 150	°C

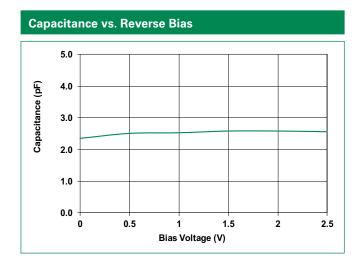
CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the component. This is a stress only rating and operation of the component at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### Electrical Characteristics (Top=25°C)

Parameter	Symbol Test Conditions		Min	Тур	Мах	Units	
Reverse Standoff Voltage	V <sub>RVVM</sub>	$I_{R} \leq 1\mu A$			2.5	V	
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = 2.5V, T = 25°C 0.1		0.1	0.5	μA	
Snap Back Voltage	V <sub>SB</sub>	I <sub>sb</sub> = 50mA	2.0			V	
Clamp Voltage		$I_{_{\rm PP}}$ = 1A, $t_{_{\rm p}}$ = 8/20µs, Any I/O to Ground		4.5			
		$I_{pp} = 10A$ , $t_p = 8/20\mu s$ , Any I/O to Ground		7.5		V	
	V <sub>c</sub>	$I_{pp} = 25A$ , $t_p = 8/20\mu s$ , Any I/O to Ground		12			
		$I_{pp} = 45A$ , $t_p = 8/20\mu$ s, Line-to-Line <sup>1</sup> , two I/O Pins connected together on each line		19			
Dynamic Resistance <sup>2</sup>	R <sub>DYN</sub>	TLP, $t_p$ =100ns, Any I/O to Ground		0.1		Ω	
ESD Withstand Voltage	V	IEC 61000-4-2 (Contact)	±30			kV	
	V <sub>ESD</sub>	IEC 61000-4-2 (Air)	±30			kV	
Diode Capacitance	C <sub>I/O to GND</sub>	Between I/O Pins and Ground V_ = 0V, f = 1MHz Between I/O Pins		2.5		pF	
	C <sub>I/O to I/O</sub>	Betweén I/O Pins V <sub>e</sub> = 0V, f = 1MHz		1.2		pF	

#### Notes:

Rating with 2 pins connected together per sugguested diagram (For example, pin1 is connected to pin 10, pin 2 is connected to Pin 9, Pin 4 is connected to pin 7 and pin 5 is connected to pin 6)
Transmission Line Pulse (TLP) with 100ns width, 2ns rise time, and average window t1=70ns to t2= 90ns



# Clamping Voltage vs. I<sub>PP</sub> (I/O to GND) 15 12 Clamp Voltage (V<sub>c</sub>) 9 6 3

10.0

Peak Pulse Current-I<sub>PP</sub> (A)

15.0

0

0.0

5.0

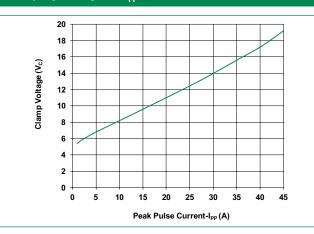
20.0

25.0

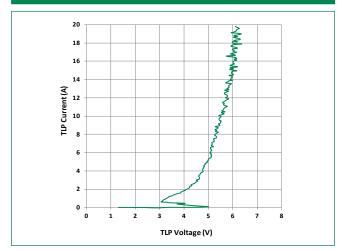


## TVS Diode Array (SPA®Diodes) Lightnign Surge Protection - SP2555NUTG

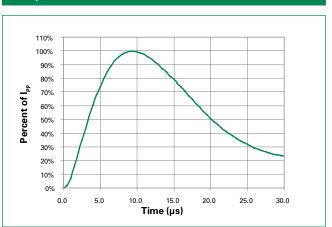
### Clamping Voltage vs. I<sub>pp</sub> (Line-to-Line)



#### Transmission Line Pulsing(TLP) Plot



#### 8/20µs Pulse Waveform

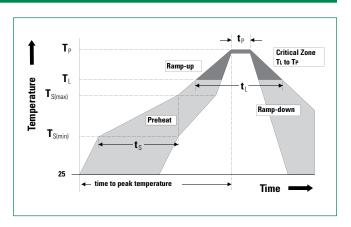




### **TVS Diode Array** (SPA®Diodes) Lightnign Surge Protection - SP2555NUTG

#### Soldering Parameters

Reflow Con	Pb – Free assembly		
Pre Heat	- Temperature Min (T <sub>s(min)</sub> )	150°C	
	- Temperature Max (T <sub>s(max</sub> )	200°C	
	- Time (min to max) (t <sub>s</sub> )	60 – 180 secs	
Average ran	np up rate (Liquidus) Temp $(T_L)$ to peak	3°C/second max	
T <sub>S(max)</sub> to T <sub>L</sub> -	3°C/second max		
Reflow	- Temperature (T <sub>L</sub> ) (Liquidus)	217°C	
	- Temperature (t <sub>L</sub> )	60 – 150 seconds	
Peak Tempe	260+ <sup>0/-5</sup> °C		
Time within	n 5°C of actual peak Temperature (t <sub>p</sub> )	20 – 40 seconds	
Ramp-down	6°C/second max		
Time 25°C t	8 minutes Max.		
Do not exce	260°C		

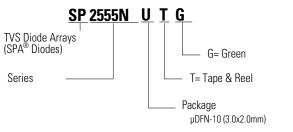


#### **Ordering Information**

Part Numbering System

Part Number	Package	Min. Order Qty.
SP2555NUTG	µDFN-10 (3.0x2.0mm)	3000

## Part Marking System

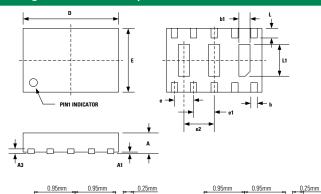


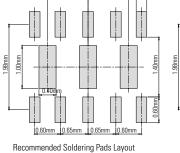


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#### Package Dimensions - µDFN-10 (3.0x2.0mm)





		φ	Ψ	Ψ	$\varphi$	Ψ.	
1.98mm	0.85mm					-	1.40mm
		<u>0.60</u>	1m 0.65	mm 0.65r	nm 0.60n		0.60mm
				tencil Ape ncil thickr		ls	

Ø

Package			DEN-10 (3)	0v2.0mm)			
JEDEC	μDFN-10 (3.0x2.0mm)						
JEDEC	MO-229						
Symbol		Villimeters		Inches			
Symbol	Min	Nom	Max	Min	Nom	Мах	
Α	0.50	0.60	0.65	0.020	0.024	0.026	
A1	0.00	0.03	0.05	0.000	0.001	0.002	
A3	0.15 Ref			0.006 Ref			
b	0.15	0.20	0.25	0.006	0.008	0.010	
b1	0.25	0.35	0.45	0.010	0.014	0.018	
D	2.90	3.00	3.10	0.114	0.118	0.122	
E	1.90	2.00	2.10	0.075	0.079	0.083	
е	0.60 BSC			0	.024 BSC		
e1	0.65 BSC			0	.026 BSC		
e2	0.95 BSC			0.037			
L	0.25	0.30	0.35	0.010	0.012	0.014	
L1	0.95	1.00	1.05	0.037	0.039	0.041	

#### Notes :

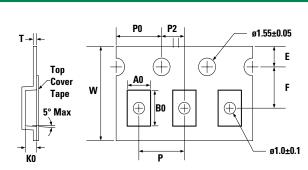
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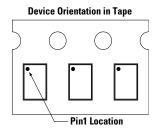
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1. All dimensions are in millimeters

Dimensions include solder plating.
Dimensions are exclusive of mold flash & metal burr

#### Tape & Reel Specification - µDFN-10 (3.0x2.0mm)





Package	µDFN-10 (3.0x2.0mm)		
Symbol	Millimeters		
A0	2.30 +/- 0.10		
B0	3.20 +/- 0.10		
E	1.75 +/- 0.10		
F	3.50 +/- 0.05		
КО	1.0 +/- 0.10		
Р	4.00 +/- 0.10		
P0	4.00 +/- 0.10		
P2	2.00 +/- 0.10		
Т	0.3 +/- 0.05		
W	8.00 +0.30/- 0.10		

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